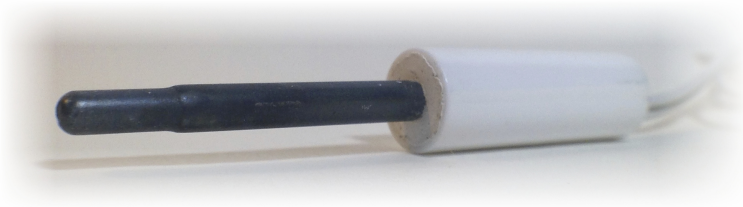
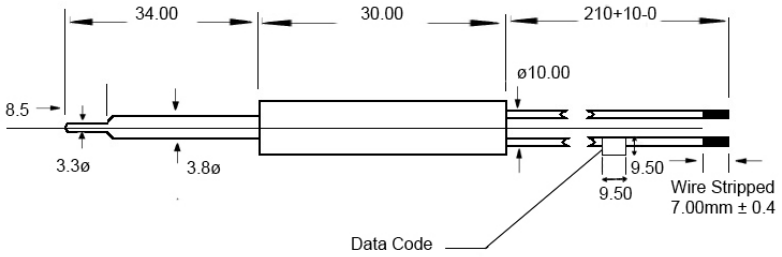
IR-Si295 Emitter Datasheet

The IR-Si series emitters are designed to supply higher temperatures and greater output compared to other IR sources. The patented silicon nitride or silicon carbide material ensures a robust design.



Note: all dimensions in mm



Note: All tolerance ± 1.00mm unless otherwise stated

Recommended (Maximum) Operating Parameters

Voltage, V	12	(14)
Temperature °C	1250	(1340)
Current, A	4.7	(5.1)
Power, W	56.4	(71.4)

Properties at Recommended Parameters

Life	5000+ Hours
Emissivity, %	80
Active Area (mm)	3.5(D) X 12(L)
Material	Silicon Nitride

IR-Si series emitters can be paired with elliptical or parabolic reflectors for a significantly more efficient collimation of energy. Windows are also available for specific transmitting ranges.

Contact Information:
Boston Electronics
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shop.boselec.com
boselec@boselec.com
+1.617.566.3821

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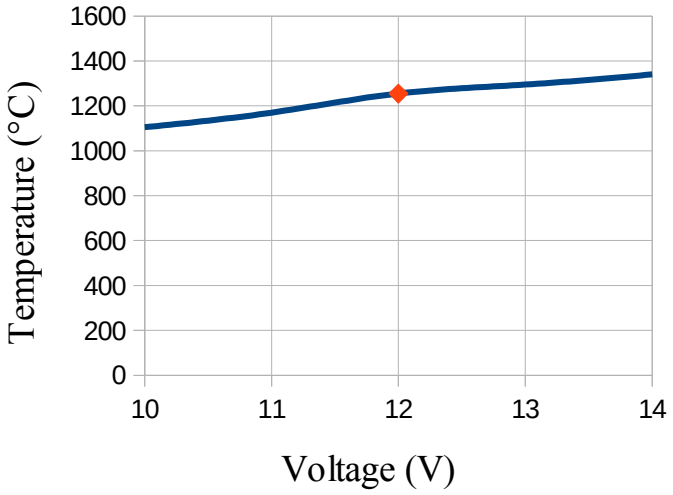
Specifications subject to change without notice.
Please visit our website for the most up to date information.

Sample Data Points

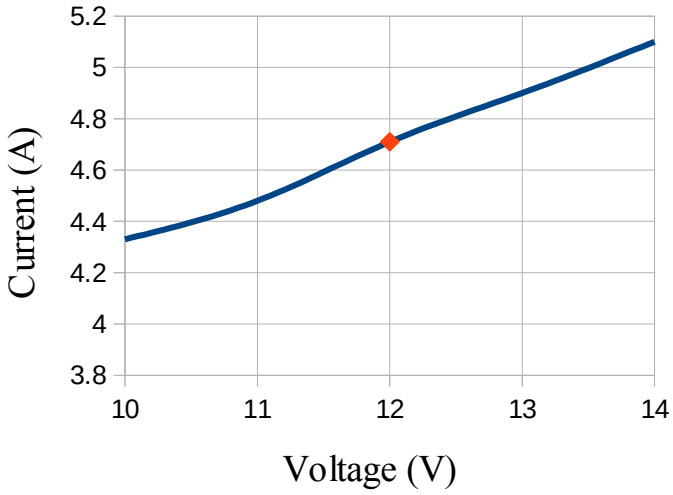
BostonElectronics

V	10	11	12	13	14
A	4.33	4.48	4.71	4.9	5.1
W	43.3	49.28	56.5	63.95	71.4
°C	1105	1170	1255	1295	1340

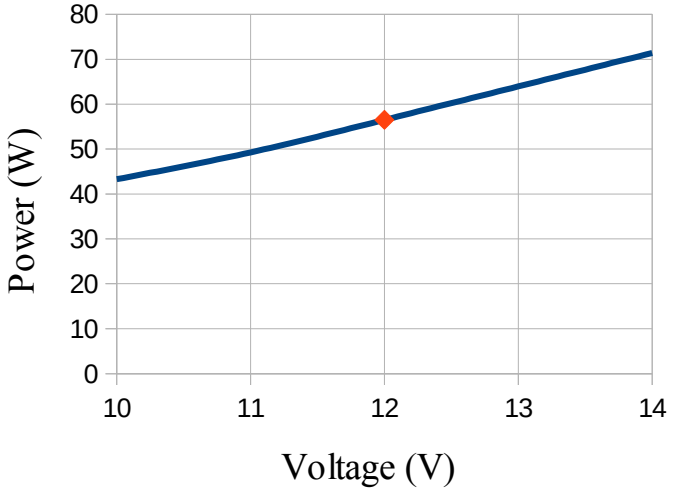
Temperature vs. Voltage



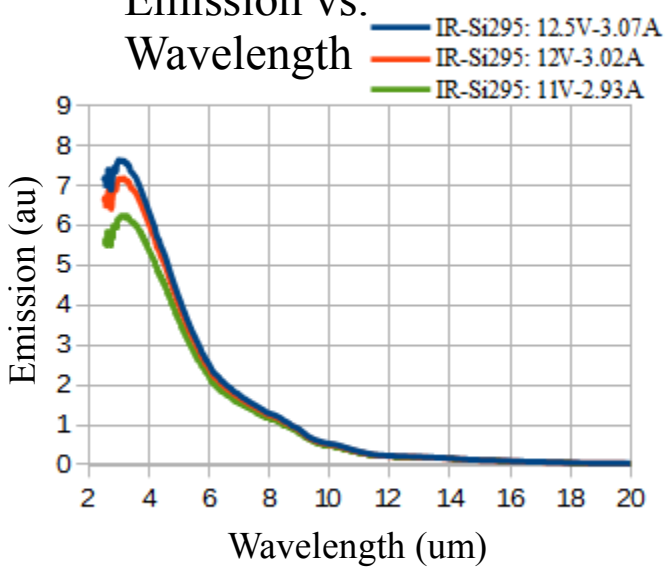
Current vs. Voltage



Power vs. Voltage



Emission vs. Wavelength



◆: Nearing Maximum Operating Parameters

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